

UNITED STATES DEPARTMENT OF COMMER **Patent and Trademark Office**

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APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO 09/517,705 03/02/00 LIANG \mathbf{C} 042390.P5771 **EXAMINER** MM91/0815 Blakely Sokoloff Taylor & Zafman LLP PAPER NUMBER ART UNIT 12400 Wilshire Boulevard 7th Floor Los Angeles CA 90025 2811 **DATE MAILED:**

08/15/01

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks



		Application No.	Applicant(s)
•	•	09/517,705	LIANG ET AL.
Office Action Summary		Examiner	Art Unit
		Steven Loke	2811
Period fo	The MAILING DATE of this communication or Reply	n appears on the cover sheet w	ith the correspondence address
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD FOR R MAILING DATE OF THIS COMMUNICATI sions of time may be available under the provisions of 37 C SIX (6) MONTHS from the mailing date of this communicatic period for reply specified above is less than thirty (30) days, period for reply is specified above, the maximum statutory are to reply within the set or extended period for reply will, by eply received by the Office later than three months after the d patent term adjustment. See 37 CFR 1.704(b).	ON. FR 1.136(a). In no event, however, may a ron. a reply within the statutory minimum of thir beriod will apply and will expire SIX (6) MON statute, cause the application to become Al	reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).
1)[Responsive to communication(s) filed or	05 January 2001 .	
2a) <u></u> □	This action is FINAL . 2b)	This action is non-final.	
3)	Since this application is in condition for a closed in accordance with the practice u		
Dispositi	on of Claims		
4) 🖂	Claim(s) 1 and 2 is/are pending in the ap	plication.	
	4a) Of the above claim(s) is/are wit	hdrawn from consideration.	
5)	Claim(s) is/are allowed.		
6)⊠	Claim(s) 1 and 2 is/are rejected.		
7)	Claim(s) is/are objected to.		
8)[Claim(s) are subject to restriction a	and/or election requirement.	
Applicati	on Papers		
9) 🗌 🤈	The specification is objected to by the Exa	miner.	
10) 🗌 🤄	The drawing(s) filed on is/are: a)□	accepted or b) objected to by t	the Examiner.
	Applicant may not request that any objection	to the drawing(s) be held in abey	ance. See 37 CFR 1.85(a).
11)	The proposed drawing correction filed on _	is: a)□ approved b)□ c	disapproved by the Examiner.
	If approved, corrected drawings are required	in reply to this Office action.	
12) 🔲	The oath or declaration is objected to by th	ne Examiner.	
Priority ι	ınder 35 U.S.C. §§ 119 and 120		
13)	Acknowledgment is made of a claim for fo	preign priority under 35 U.S.C.	§ 119(a)-(d) or (f).
a)	☐ All b)☐ Some * c)☐ None of:		
	1. Certified copies of the priority docu	ments have been received.	
	2. \square Certified copies of the priority docu	ments have been received in A	Application No
* 5	3. Copies of the certified copies of the application from the Internation See the attached detailed Office action for	al Bureau (PCT Rule 17.2(a)).	_
	cknowledgment is made of a claim for do	<u>.</u>	
_a) ☐ The translation of the foreign languag Acknowledgment is made of a claim for do	e provisional application has b	een received.
, — Attachmen		The state of the s	. 00
1) Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-94 nation Disclosure Statement(s) (PTO-1449) Paper N	8) 5) Notice of	Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-152)

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Since the supplemental preliminary amendment filed on 1/5/01 has canceled the method claims 3-15, the restriction mailed on 2/13/01 is withdrawn from the application.

The abstract of the disclosure is objected to because the abstract should disclose the structure of the device instead of the method to make the device. Correction is required.

The disclosure is objected to because of the following informalities:

In page 9, line 26, change "thickness a" to "a thickness".

Since the written description (page 12, lines 10-11) discloses molybdenum silicide has a Fermi level of 4.25 eV (N-type), it is unclear why molybdenum silicide is used as a gate electrode for PMOS device (page 15, lines 22-26).

Appropriate correction is required.

Claims 1 and 2 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 1, lines 2-3, "a first metal gate electrode overlying a over a first gate dielectric" is unclear whether it is being referred to "a first metal gate electrode overlying a first gate dielectric".

In claim 2, line 1, "The integrated circuit device" has no antecedent basis.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

⁽b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

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Claims 1 and 2 are rejected under 35 U.S.C. 102(b) as being clearly anticipated by Dash et al.

In regards to claim 1, Dash et al. shows all the elements of the claimed invention in fig. 9. It is a circuit device comprising: a first transistor (NMOS) including a first metal gate electrode [56] made of aluminum overlying a first gate dielectric [14'] on a first area of a semiconductor substrate and having a work function (4.1 eV) corresponding to the work function of the N-type silicon; and a second transistor (PMOS) complementary to the first transistor including a second metal gate electrode [50] made of platinum silicide over a second gate dielectric [14"] on a second area of a semiconductor substrate and having a work function (5.7 eV) corresponding to the work function of the P-type silicon.

In regards to claim 2, Dash et al. discloses the first metal gate electrode [56] (aluminum) is a pure metal.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven Loke whose telephone number is (703) 308-4920. The examiner can normally be reached on 7:45 am to 5:15 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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August 12, 2001

Steven Loke Primary Examiner

Steven Sohe